

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,112,495 B2
APPLICATION NO. : 10/729095
DATED : September 26, 2006
INVENTOR(S) : Ko et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Page 2, Column 1, line 65; delete "6,872,810" insert --6,872,610--
Page 2, Column 2, line 27; delete "TEZUKA, T., et al. "High Performance Strained Si-on-Insulator MOSFETs With Higher Strain in Si Channel Using Double SiGe Heterostructures," IEEE Transactions on Electron Devices, vol. 49, No. 1, (Jan. 2002), pp. 7-14." insert --TEZUKA, T., et al., "High-Performance Strained Si-on-Insulator MOSFETs by Novel Fabrication Processes Utilizing Ge-Condensation Technique," Symposium On VLSI Technology Digest of Technical Papers, (2002), pp. 96-97.--
Column 5, line 6; delete "patent application" insert --Patent Application--
Column 6, line 24; delete "suicides" insert --silicides--
Column 17, line 2; delete "cobalt suicide" insert --cobalt silicide--
Column 17, line 2; delete "nickel suicide" insert --nickel silicide--
Column 17, line 40; delete "suicide" insert --silicide--
Column 17, line 42; delete "stank" insert --stack--

Signed and Sealed this

Seventeenth Day of July, 2007

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looped initial "J" and a distinct "D".

JON W. DUDAS
Director of the United States Patent and Trademark Office